NPN Triple Diffused Planar Silicon Transistor



2SC3749

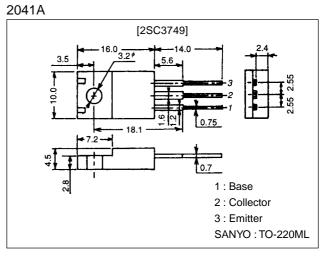
# **500V/3A Switching Regulator Applications**

## Features

- $\cdot$  High breakdown voltage and high reliability.
- · Fast switching speed.
- $\cdot$  Wide ASO.
- · Adoption of MBIT process.
- · Micaless package facilitating mounting.

# **Package Dimensions**

unit:mm



# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		800	V
Collector-to-Emitter Voltage	VCEO		500	V
Emitter-to-Base Voltage	VEBO		7	V
Collector Current	IC		3	A
Collector Current (Pulse)	I <sub>CP</sub>	PW≤300µs, Duty Cycle≤10%	6	A
Base Current	Ι <sub>Β</sub>		1	Α
Collector Dissipation	PC	Tc=25°C	25	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Electrical Characteristics at Ta = 25°C**

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	ICBO	V <sub>CB</sub> =500V, I <sub>E</sub> =0			10	μΑ
Emitter Cutoff Current	IEBO	$V_{EB}=5V, I_{C}=0$			10	μA
DC Current Gain	h <sub>FE</sub> 1	$V_{CE}=5V, I_{C}=0.3A$	15*		50*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =5V, I <sub>C</sub> =1.5A	8			
Gain-Bandwidth Product	fT	V <sub>CE</sub> =10V, I <sub>C</sub> =0.3A		18		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		50		pF

\*: The h<sub>FE</sub>1 of the 2SC3749 is classified as follows. When specifying the h<sub>FE</sub>1 rank, specify two ranks or more in principle.

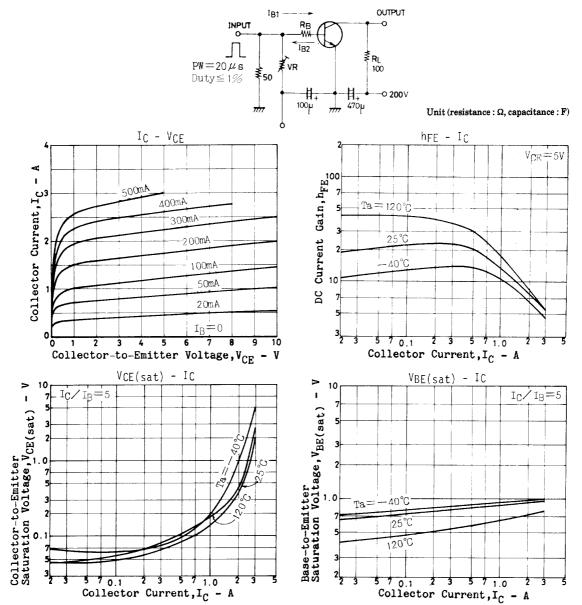
15 L 30 20 M 40 30 N 50

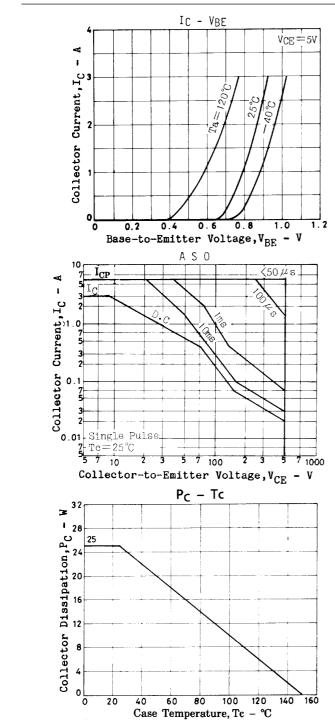
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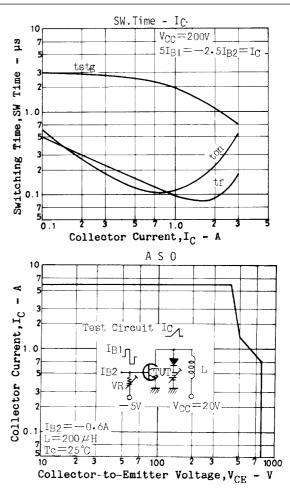
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	VCE(sat)	I <sub>C</sub> =1.5A, I <sub>B</sub> =0.3A			1.0	V
Base-to-Emitter Saturation Voltage	VBE(sat)	I <sub>C</sub> =1.5A, I <sub>B</sub> =0.3A			1.5	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =1mA, I <sub>E</sub> =0	800			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =5mA, R <sub>BE</sub> =∞	500			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =1mA, I <sub>C</sub> =0	7			V
Collector-to-Emitter Sustain Voltage	VCEX(sus)	I <sub>C</sub> =1.5A, I <sub>B1</sub> =-I <sub>B2</sub> =0.6A, L=2mH, Clamped	500			V
Turn-ON Time	ton	$V_{CC}=200V, 5I_{B1}=-2.5I_{B2}=I_{C}=2A, R_{L}=100\Omega$			0.5	μs
Storage Time	<sup>t</sup> stg	$V_{CC}=200V, 5I_{B1}=-2.5I_{B2}=I_{C}=2A, R_{L}=100\Omega$			3.0	μs
Fall Time	t <sub>f</sub>	$V_{CC}$ =200V, 5I <sub>B1</sub> =-2.5I <sub>B2</sub> =I <sub>C</sub> =2A, R <sub>L</sub> =100\Omega			0.3	μs

### **Switching Time Test Circuit**







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